

In the Specification:

On page 2, line 7 between "U.S. Pat. No." and "to Sato et al." please insert -- 5,379,139 --.

On page 8, line 6 please delete "1000 and 2000" and insert therefor -- 500 and 2000 --.

On page 8, line 8 between "substrate 20." and "Next, as shown in Fig. 3," please insert the following.

a1
-- The opaque pads 21 can also be formed from black photosensitive material having a thickness of between about 0.1 and 2.0 microns. --

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a2
On page 8, line 9 between "positive photoresist 22" and "is formed" please insert -- , having a thickness of between about 1 and 3 microns, --. On page 8, line 23 between "positive photoresist 24" and "is formed" please insert -- , having a thickness of between about 1 and 3 microns, --.
a3

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a4
On page 9, line 19 between "sufficient spacer height." and "Since each layer" please insert the following.
-- In like manner third photoresist pads can be formed on the second photoresist pads. A third layer of positive photoresist, having a thickness of between about 0.5 and 3

microns, is formed on the first surface of the first transparent substrate covering the opaque pads, the first photoresist pads, and the second photoresist pads. A light beam is again passed through the second surface of the first transparent substrate to expose the third layer of positive photoresist. The opaque pads again act as a mask so that when the exposed third layer of positive photoresist is developed photoresist remains only on the second photoresist pads forming third photoresist pads. The third photoresist pads are self aligned to the opaque pads, the first photoresist pads, and the second photoresist pads so that there are no alignment problems. In like manner fourth photoresist pads can be formed on the third photoresist pads. A fourth layer of positive photoresist, having a thickness of between about 0.2 and 3 microns, is formed on the first surface of the first transparent substrate covering the opaque pads, the first photoresist pads, the second photoresist pads, and the third photoresist pads. A light beam is again passed through the second surface of the first transparent substrate to expose the fourth layer of positive photoresist. The opaque pads again act as a mask so that when the exposed fourth layer of positive photoresist is developed photoresist remains only on the third photoresist pads forming fourth photoresist pads. The fourth photoresist pads are self aligned to the opaque pads, the first photoresist pads, the second photoresist pads, and